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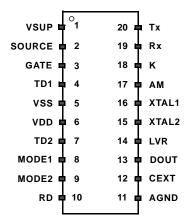
Data Sheet: Product Preview

Document Number: SC33690DS Rev. 5, 02/2007



SOIC-20

Pin Connections



ORDERING INFORMATION

Device	Operating Junction Temperature Range	Package
MC33690DW	T _J = -40°C to 125°C	SOIC 20
MC33690DWE	$TJ = -40^{\circ}C$ to 125°C	SOIC 20 (ROHS)

Reader Circuit The standalone tag reader circuit (STARC) is an integrated circuit dedicated to the automotive immobilizer applications.

MC33690 Standalone Tag

It combines the antenna drivers and demodulator necessary to interface with a transponder.

A low dropout voltage regulator and a physical interface fully compatible with the ISO 9141 norm are also available. The STARC is fabricated with the SMARTMOSTM3.5

technology. This process is a double layer metal $1.4\mu m$ 45V technology, combining CMOS and bipolar devices.

- Contactless 125 kHz tag reader module:
 - Self synchronous sample and hold demodulator
 - Amplitude or phase modulation detection
 - High sensitivity
 - Fast read after write demodulator settling time
 - Low resistance and high current antenna drivers, 2W @ 150mA (typ.)
 - Bidirectionnal data transmission
 - Multi-tag, multi-scheme operation
- Low dropout voltage regulator:
 - Wide input supply voltage range from 5.5V up to 40V
 - Output current capability up to 150mA DC with an external power transistor
 - 5V output voltage with a ±5% accuracy
 - Low voltage reset function
 - Low current consumption in standby mode:
 - 300µA (typ.)
- ISO 9141 transmitter and receiver module:
 - Input voltage thresholds ratiometric to the supply voltage
 - Current limitation
 - Output slew rate control
 - No external protection device required

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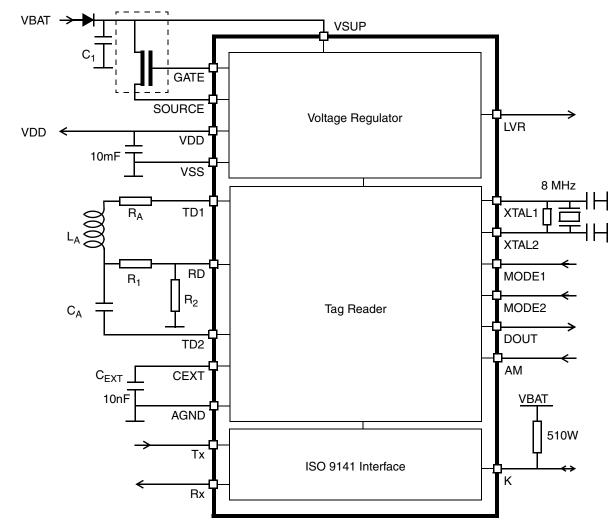
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NP



Optional: External N channel MOS required for sourced current > 50mA. A recommended reference is MMFT 3055VL from Freescale.

Figure 1. Standalone Tag Reader Circuit



Rating	Symbol	Value	Unit	
Supply voltage	V _{SUP}	V _{SS} -0.3 to +40	V	
Supply voltage without using the voltage regulator $(V_{SUP} = V_{DD})$	V _{DD}	V _{SS} –0.3 to +7	V	
Voltage on SOURCE	—	V _{SS} -0.3 to +40	V	
Current into/from GATE	—	0	mA	
Voltage on GATE	_	V _{SS} -0.3	V	
Voltage on pins: MODE1/2, CEXT, DOUT, LVR, XTAL1/2, Rx, Tx	-	V_{SS} –0.3 to V_{DD} +0.3	V	
Voltage on RD	_	±10	V	
Voltage on K and AM	_	V _{SS} –3 to 40	V	
Current on TD1 and TD2 (Drivers on and off)	_	±300	mA	
Voltage on AGND		V _{SS} ±0.3	V	
ESD voltage capability ¹		±2000	V	
ESD voltage capability ¹		±200	V	
Solder heat resistance test (10s)		260	°C	
Junction temperature	TJ	170	°C	
Storage temperature	T _s	-65 to +150	°C	

Table 1. Maximum Ratings

¹ Human Body Model, AEC-Q100-002 Rev. C; Machine Model, AEC-Q100-003 Rev. E.

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Junction to ambient thermal resistance (SOIC20)	R _{th}	80	°C/W

Table 3. Pin Function Descriptions

Pin	Function	Description
1	VSUP	Power supply
2	SOURCE	External N channel transistor source
3	GATE	External N channel transistor gate
4	TD1	Antenna driver 1 output
5	VSS	Power and digital ground
6	VDD	Voltage regulator output
7	TD2	Antenna driver 2 output
8	MODE1	Mode selection input 1
9	MODE2	Mode selection input 2
10	RD	Demodulator input

	_			

11	AGND	Demodulator ground
12	CEXT	Comparator reference input
13	DOUT	Demodulator output (5V)
14	LVR	Low Voltage Reset input/output
15	XTAL2	Oscillator output
16	XTAL1	Oscillator input
17	AM	Amplitude modulation input
18	К	ISO 9141 transmitter output and receiver input
19	Rx	ISO 9141 receiver monitor output
20	Tx	ISO 9141 transmitter input

Table 3. Pin Function Descriptions (continued)

1 Description

1.1 Tag Reader Module

The tag reader module is dedicated for automotive or industrial applications where information has to be transmitted contactless. The tag reader module is a write/read (challenge/response) controller for applications that a demand high security level.

The tag reader module is connected to a serial-tuned LC circuit that generates a magnetic field power supplying the tag. The use of a synchronous sample and hold technique allows communication with all available tags using admittance switching producing absorption of the RF field.

Load amplitude or phase shift modulation can be detected at high bit rates up to 8 kHz. The typical operational carrier frequency of the tag reader module with an 8 MHz clock is 125 kHz.



Read Function

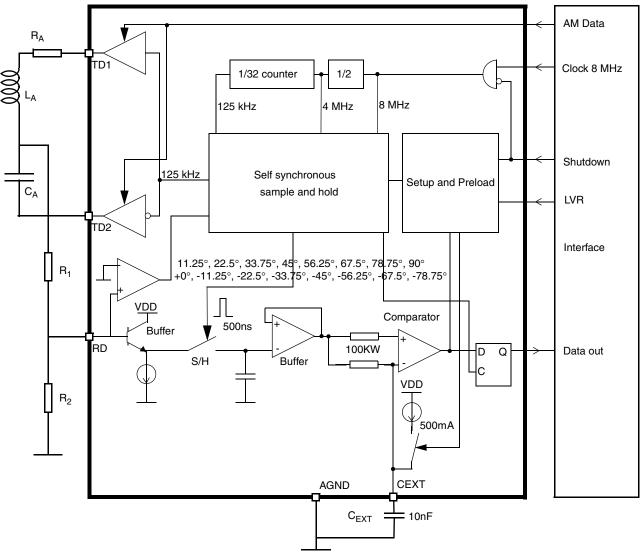


Figure 2. Tag Reader Block Diagram

2 Read Function

When answering to the base station, a transponder generates an absorption modulation of the magnetic field. It results in an amplitude/phase modulation of the current across the antenna. This information is picked up at the antenna tap point between the coil and the capacitor. An external resistive ladder down scales this voltage to a level compatible with the demodulator input voltage range (see Section 15, "Tag Reader").

The demodulator (see Figure 2) consists of:

- an input stage (emitter follower)
- a sample and hold circuit
- a voltage follower
- a low offset voltage comparator

The sampling time is automatically set to take into account a phase shift due to the tolerances of the antenna components (L and C) and of the oscillator. The allowed phase shift measured at the input RD ranges from -45° to $+45^{\circ}$. Assuming that the phase





reference is the falling edge of the driving signal TD1, this leads to a sampling time phase ranging from -78.75° to 90° with discrete steps of 11.25° . After reset condition, the sampling time phase is $+11.25^{\circ}$.

The antenna phase shift evaluation is only done after each wake-up command or after reset. This is necessary to obtain the best demodulator performances.

To ensure a fast demodulator settling time after wake-up, reset, or a write sequence, the external capacitor CEXT is preloaded at its working voltage. This preset occurs 256µs after switching the antenna drivers on and its duration is 128µs. After wake-up or reset, the preset has the same duration, but begins 518µs after clock settling. After power on reset, VSUP must meet the minimum specified value, enabling the nominal operation of VDD, before the start of the preset. Otherwise, the preset must be done through a standby/wake-up sequence.

3 Write Function

Whatever the selected configuration (see Section 6, "Communication Modes Description"), the write function is achieved by switching on/off the output drivers TD1/2. After the drivers have been set in high impedance, the load current flows alternatively through the internal diodes to VSS and to VDD (see Figure 3).

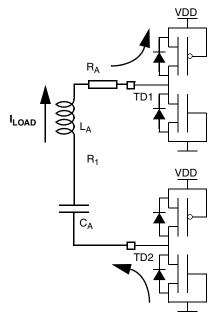


Figure 3. Current Flow When Buffers are Switched Off

4 Voltage Regulator

The low dropout voltage regulator provides a regulated 5V supply for the internal circuitry. It can also supply external peripherals or sensors. The input supply voltage ranges from 5.5V to over 40V.

This voltage regulator uses a series combination of high voltage LDMOS and low voltage PMOS transistors to provide regulation. An external low ESR capacitor is required for the regulator stability.

The maximum average current is limited by the power dissipation capability of the SO 20 package. This limitation can be overcome by connecting an external N channel MOS parallel with the internal LDMOS. The threshold voltage of this transistor must be lower than the one of the internal LDMOS (1.95V typ.) to prevent the current from flowing into the LDMOS. Its breakdown voltage must be higher than the maximum supply voltage.

A low-voltage reset function monitors the VDD output. An internal 10μ A pull-up current source allows, when an external capacitor is connected between LVR and GND, to generate delays at power up (5ms typ. with C_{Reset}=22nF). The LVR pin is

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ISO 9141 Physical Interface

also the input generating the internal reset signal. Applying a logic low level on this pin resets the circuit, all the internal flip flops are reset, and drivers TD1/2 are switched on.

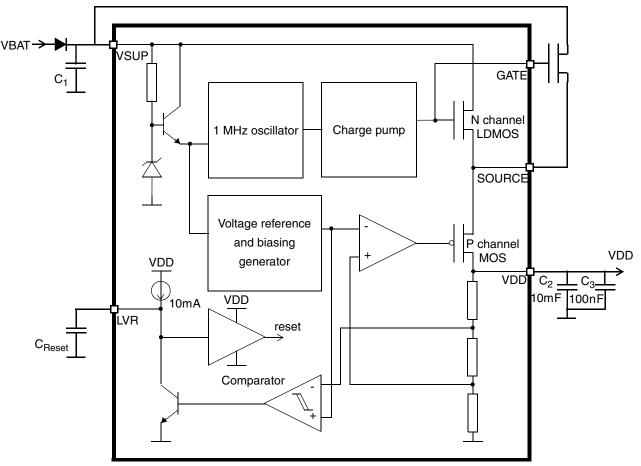


Figure 4. Voltage Regulator Block Diagram

5 ISO 9141 Physical Interface

This interface module is fully compatible with the ISO 9141 norm describing the diagnosis line. It includes one transmitter (pin K) and two receivers (pins K and AM).

The input stages consist of high-voltage CMOS triggers. The thresholds are ratiometric to VSUP. A ground referenced current source $(2.5\mu A \text{ typ.})$ pulls down the input when unconnected.

When a negative voltage is applied on the K or AM lines, the input current is internally limited by a $2k\Omega$ resistor (typ.) in series with a diode.

A current limitation allows the transmitter to drive any capacitive load and protects against short circuit to the battery voltage. An overtemperature protection shuts the driver down when the junction temperature exceeds 150°C (typ). After shutdown by the overtemperature protection, the driver can be switched on again if the junction temperature has decreased below the threshold and by applying an off/on command, coming from the demodulator in configurations A and B, or directly applied on the input Tx in configuration C (see Table 4).

The electromagnetic emission is reduced because of the voltage slew rate control (5V/ μ s typ.).



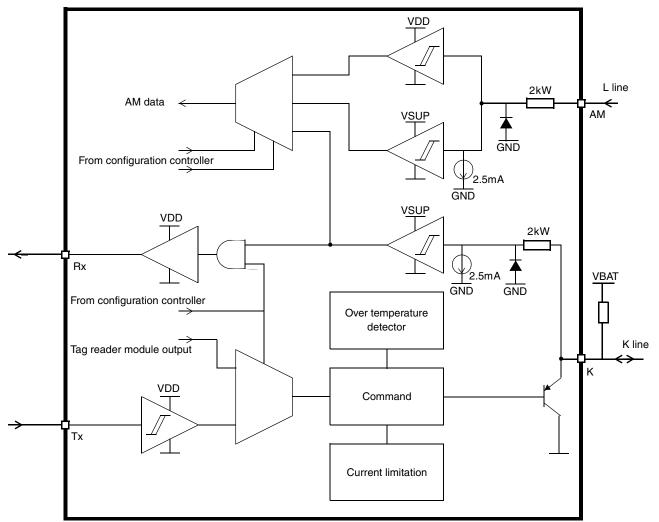


Figure 5. ISO 9141 Interface

6 Communication Modes Description

The STARC offers three different communication modes. Therefore, it can be used as a standalone circuit connected to an electronic control unit (ECU) through a bus line or it can be directly connected to a microcontroller in case of a single board architecture.

9



Standalone Configuration with One-Wire Bus

Configuration		Configuration Pins		Pin Status Function Description	
Туре	Bus Type	Name	Mode1	Mode2	
Standalone	1 wire (VBAT)	A	0	0	K output/input: • demodulator output • amplitude modulation input • shutdown/wake-up AM must be connected to VSUP DOUT forces a low level
	2 wires (VBAT)	В	0	1	K output: • demodulator output AM input: • amplitude modulation input • shutdown/wake-up DOUT forces a low level
Direct Connection to a MCU	2 wires (VDD)	С	1	x	DOUT output: • demodulator output AM input: • amplitude modulation input MODE2 input: • shutdown/wake-up
				1	K output/input (standalone ISO 9141 interface): • driven by Tx and monitored by Rx
				0	K input (standalone ISO 9141 interface): • monitored by Rx • Tx disabled

Table 4. Communication Modes Description

7 Standalone Configuration with One-Wire Bus

When a low level is applied on pins MODE1 and MODE2, the circuit is in configuration A (see Figure 24). After power on, the circuit is set into read mode. The demodulator output is directly routed to the ISO 9141 interface output K.

The circuit can be set into write mode at anytime by violation of all possible patterns on the single wire bus during more than 1ms. Then, the K line achieves the amplitude modulation by switching on/off both antenna drivers.

After 1ms of inactivity at the end of the challenge phase (bus in idle recessive one state), the circuit is set back into read mode.

The circuit can be put into standby mode by forcing the K line at zero during more than 2 ms after entering the write mode. After the K line is released, the circuit sends an acknowledge pulse before entering into standby mode. In standby mode, the oscillator and most of the internal biasing currents are switched off. Therefore, the functions (tag reader, ISO 9141 driver) are inactive except the voltage regulator and the ISO 9141 receiver on pin K. The driver output TD1 forces a low level and TD2 forces a high level. A rising edge on K wakes up the circuit. After completion of the wake-up sequence, the circuit is automatically set in read mode.

In configuration A, DOUT and Rx outputs always force a low level and Tx is disabled.



Standalone Configuration with One-Wire Bus

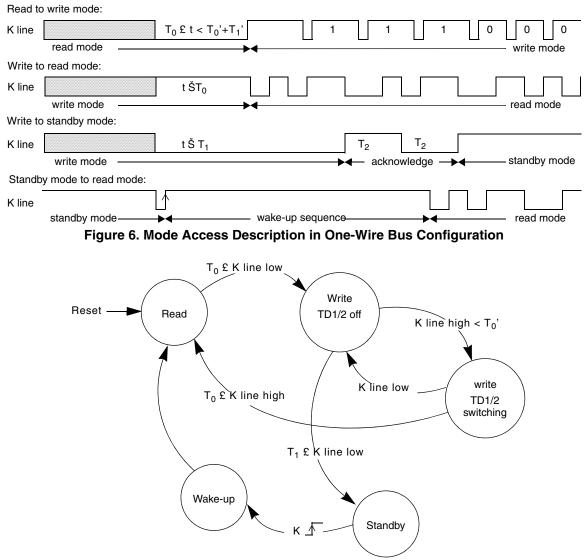


Figure 7. Configuration A State Diagram

7.1 Timing Definitions for a 8 MHz Crystal

The timing definitions for a 8 MHz crystal are:

- T_{ref} is crystal oscillator period (125 ns typ.)
- $T_0 = 8064.T_{ref} = 1.008 ms typ.$
- T_0 '=7932. T_{ref} = 0.992ms typ.
- $T_1 = 16256.T_{ref} = 2.032ms$ typ.
- T_1 '=16128. T_{ref} = 2.016ms typ.
- $T_2 = 4096.T_{ref} = 512 \mu s$ typ.

 T_0 is the minimum time required to guarantee the device toggles from read to write (or from write to read). However, the STARC may toggle from read to write (or from write to read) between T_0 and T_0 '.

 T_1 is the minimum time required to guarantee the device toggles from write to standby. However, the STARC may toggle in standby between T_1 and T_1 '.

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Standalone Configuration with Two-Wire Bus

Standalone Configuration with Two-Wire Bus 8

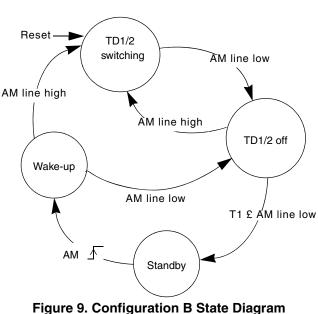
When a low level is applied on MODE1 and a high level on MODE2, the circuit is in configuration B (see Figure 25). The K pin is set as an output sending the demodulated data.

The AM pin is set as a VSUP referenced input pin receiving the amplitude modulation and the shutdown/wake-up commands. Forcing high and low levels on AM achieves the amplitude modulation by switching on/off both antenna drivers. This amplitude modulation can be monitored on the K output and allows antenna short and open circuit diagnosis. The circuit can be put into standby mode by forcing the AM line at zero during more than 2 ms. The circuit sends an acknowledge pulse before entering into standby mode.

In standby mode, the oscillator and most of the internal biasing currents are switched off. Therefore, the functions (tag reader and ISO 9141 driver) are inactive except for the voltage regulator and the ISO 9141 receiver on pin AM. The driver output TD1 forces a low level and TD2 a high level. A rising edge on AM wakes up the circuit. After completion of the wake-up sequence, the circuit is automatically set in read mode.

Read and write sequences: data write modulation drivers on drivers off 1 AM line data read data write K line 1 0 AM line monitoring Entering into standby mode: AM line t Š T1 standby mode acknowledge K line T1 Τ2 Τ2 Coming out of standby mode: AM line standby mode. wake-up sequence data read K line Figure 8. Modes Access Description in Two-wire Bus Configuration

In configuration B, DOUT and Rx outputs always force a low level and Tx is disabled.





9 Direct Connection to a Microcontroller Configuration

When a high level is applied on MODE1, the circuit is in configuration C (see Figure 26). The demodulated data are sent through DOUT.

The AM pin is set as a VDD referenced input pin receiving the AM command. Forcing high and low levels on AM achieves the amplitude modulation by switching on/off both antenna drivers. Meanwhile, this amplitude modulation can be monitored on DOUT. This allows antenna short and open circuit diagnosis.

The circuit can be put into standby mode by applying a low level on the MODE2 pin. In standby mode, the oscillator and most of the internal biasing currents are switched off. Therefore, the functions (tag reader and ISO 9141 interface) are inactive except for the voltage regulator. The driver outputs TD1 and TD2 are frozen in their state (high or low level) before entering into standby mode. DOUT forces a low level.

The ISO 9141 interface K is standalone and can be directly controlled by the input pin Tx and monitored by the output Rx. Applying a logic high level on Tx switches the output driver K on (dominant zero state when an external pull-up resistor is connected between K and VBAT). Applying a logic low level turns the driver off (one recessive state).

Rx monitors the voltage at the K pin. When the voltage is below the low threshold voltage, Rx forces a logic low level. When the voltage is above the high threshold voltage, Rx forces a logic high level.

In standby mode, Tx is disabled and Rx output monitors the voltage at the K pin.

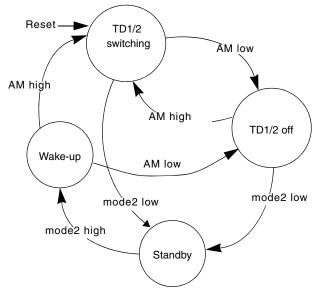


Figure 10. Configuration C State Diagram

10 Electrical Characteristics

Typical values reflect average measurements at $V_{SUP}=12V$ and $T_J=25^{\circ}C$.

11 Supply Current

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted.





Voltage Regulator

Parameter		Symbol	Test Conditions and Comments	Min	Тур	Max	Unit	Туре
	Pin VSUP							
9.1	Standby mode current	I _{SUP1}	_	_	300	500	μA	
9.2	Operating mode current	I _{SUP2}	Circuit in configuration C No current sunk from VDD Drivers TD1/2 switched off Tx forced to low		1.5	2.5	mA	—

Table 5. Supply Current Specifications

12 Voltage Regulator

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted

	Parameter	Symbol	Test Conditions and Comments	Min	Тур	Max	Unit	Туре
		Pi	ins VSUP and VDD				•	
1.1	Output Voltage (5.5V \leq V _{SUP} \leq 40V)	V _{VDD1}	Without external MOS	4.75	5.0	5.25	V	—
1.3	Total Output Current	I _{VDD1}	transistor, $I_{OUT} \le 50 mA$			50	mA	—
1.5	Load Regulation	V _{LoadReg1}	Without external MOS transistor, 1 to 50mA I _{OUT} change	_	20	60	mV	—
1.9	Output Voltage (5.5V \leq V _{SUP} \leq 40V)	V _{VDD2}	With external MOS transistor,	4.7	5.0	5.3	V	—
1.11	Total Output Current	I _{VDD2}	I _{OUT} ≤ 150mA	_	_	150	mA	—
			The stability is ensured with a decoupling capacitor between VDD and VSS: $C_{OUT} \ge 10 \mu F$ with ESR $\le 3\Omega$.					
			The current capability can be increased up to 150mA by using an external N channel MOS transistor (see Figure 1). The main characteristics for choosing this component are VT < 1.8V and BVDSS > 40V					
1.6	Load Regulation	V _{LoadReg2}	With external MOS transistor,1 to 150mA I _{OUT} change	_	65	150	mV	—
1.4	Line Regulation (6V \leq V _{SUP} \leq 16V)	V _{LineReg}	I _{OUT} = 1mA	_	_	_	mV	—

Table 6. Voltage Regulator Specifications

13 Low-Voltage Reset

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted



	Parameter	Symbol	Test Conditions and Comments	Min	Тур	Max	Unit	Туре		
	Pin LVR									
1.6	Low Voltage Reset Low Threshold	V _{LVRON}	Because the voltage regulator	4.1	4.35	4.6	V	—		
1.7	Low Voltage Reset Hysteresis	V _{LVRH}	and the low-voltage reset are using the same internal voltage reference, the low-voltage reset occurs only when the voltage regulator is out of regulation. See Figure 11	50	100	150	mV	_		
1.12	Pull-up Current	I _{LVRUP}	V _{LVR} = 2.5V	5	10	15	μA	—		
1.13	Output Resistance in reset condition	R _{LVR}	V _{LVR} = 2.5V	200	370	500	Ω	—		
1.14	Input Low Voltage	V _{ILLVR}	_	0	—	0.3 x V _{DD}	V	—		
1.15	Input High Voltage	V _{IHLVR}	_	0.7 x V _{DD}	—	V _{DD}	V	—		



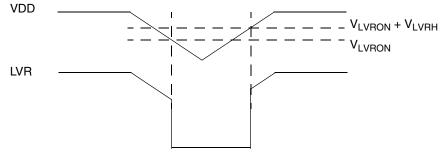


Figure 11. Low Voltage Reset Waveform

14 Oscillator

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted

Table 8. Oscillator Specifications

	Characteristic	Symbol	Test Condition and Comments	Min	Тур	Max	Unit	Туре
		F	Pins XTAL1, XTAL2					
8.0	Input Capacitance	C _{XTAL1}	$V_{XTAL1} = 2.5V$	—	5	—	pF	
8.1	Voltage gain V_{XTAL2} / V_{XTAL1}	A _{OSC}	$V_{XTAL1} = 2.5V$		25		—	
8.3	Clock input level	V _{XTAL1}	This level ensures the circuit operation with an 8 MHz clock. It is applied through a capacitive coupling. A $1M\Omega$ resistor connected between XTAL1 and XTAL2 biases the oscillator input.	1.5	_	V _{DD}	Vpp	_



Tag Reader

15 Tag Reader

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted

		ag noudor opcomodione					
Parameter	Symbol	Test Conditions and Comments	Min	Тур	Max	Unit	Туре
	De	emodulator (pin RD)					
Input Voltage Range	V _{INRD}	—	3	4	5	V	
Input Modulation Frequency	F _{MOD}	—	0.5	4	8	kHz	—
Demodulator Sensitivity	V _{SENSE1}	$\begin{array}{l} 6.5 V \leq V_{SUP} \leq 16 V \\ \text{Sensitivity is measured in the} \\ \text{following application} \\ \text{conditions: } I_{ANTENNA} = 50 \text{mA} \\ \text{peak, } V_{RD} = 4 V \text{ peak,} \\ \text{C}_{EXT} = 10 \text{nF, and square wave} \\ \text{modulation } F_{MOD} = F_{TD1}/32. \\ \text{See Figure 12} \end{array}$	_	5	15	mV	
Demodulator Sensitivity	V _{SENSE2}	$\begin{array}{l} 6V \leq V_{SUP} < 6.5V \\ \text{The sensitivity is measured in} \\ \text{the following application} \\ \text{conditions:} \\ I_{ANTENNA} = 50\text{mA peak}, \\ V_{RD} = 4V \text{ peak}, C_{EXT} = 10\text{nF}, \\ \text{and square wave modulation} \\ F_{MOD} = F_{TD1}/32 \\ \text{See Figure 12} \end{array}$	_	7	30	mV	
Demodulation Delay	t _{Demod}	Configuration C Not including the delay due to the slew rate of the K output for configurations A and B See figure 12	_	7.5	10	μs	
After Write Pulse Settling Time	t _{Settling1}	—	—	394	400	μs	—
Recovery Time after wake-up or reset from clock stable to demodulator valid output	t _{Settling2}	$\begin{array}{c} \mbox{Clock stable condition implies} \\ V_{XTAL1} \mbox{ meets the specification} \\ (see page \ 15). \end{array}$	_	646	700	μS	
	Dri	vers (pins TD1, TD2)					
Output Carrier Frequency to Crystal Frequency Ratio	R _{FTD/FXT} AL	—	—	64	—	—	_
Turn on/off Delay	t _{on/off}	—	—	—	250	ns	—
Driver1/2 Low Side Out. Resistance	R _{TDL}	I _{LOAD} = 150mA DC	_	2.4	4	Ω	—
Driver1/2 High Side Out. Resistance	R _{TDH}	I _{LOAD} = -150mA DC	_	2.1	4	Ω	
	Parameter Input Voltage Range Input Modulation Frequency Demodulator Sensitivity Demodulator Sensitivity Demodulator Sensitivity Demodulator Sensitivity Demodulator Sensitivity Demodulator Sensitivity Output Carrier Frequency to Crystal Frequency Ratio Turn on/off Delay Driver1/2 Low Side Out. Resistance	ParameterSymbolInput Voltage RangeVINRDInput Modulation FrequencyFMODDemodulator SensitivityVSENSE1Demodulator SensitivityVSENSE2Demodulator SensitivityVSENSE2Demodulator SensitivityVSENSE2Demodulator DelaytDemodulatorAfter Write Pulse Settling TimetSettling1Recovery Time after wake-up or reset from clock stable to demodulator valid outputtSettling2Output Carrier Frequency to Crystal Frequency RatioRFTD/FXT ALTurn on/off Delayton/off Driver1/2 Low Side Out. ResistanceRTD/EXT	Parameter Symbol and Comments Input Voltage Range VINRD — Input Modulation Frequency F _{MOD} — Demodulator Sensitivity V _{SENSE1} 6.5V ≤ V _{SUP} ≤ 16V Sensitivity is measured in the following application conditions: I _{ANTENNA} = 50mA peak, V _{RD} = 4V peak, C _{EXT} = 10nF, and square wave modulator Sensitivity V _{SENSE2} 6V ≤ V _{SUP} < 6.5V	Parameter Symbol Test Conditions and Comments Min Input Voltage Range VINRD — 3 Input Modulation Frequency FMOD — 0.5 Demodulator Sensitivity V _{SENSE1} 6.5V ≤ V _{SUP} ≤ 16V — Demodulator Sensitivity V _{SENSE1} 6.5V ≤ V _{SUP} ≤ 16V — Demodulator Sensitivity V _{SENSE1} 6.5V ≤ V _{SUP} ≤ 16V — Demodulator Sensitivity V _{SENSE2} 6.5V ≤ V _{SUP} ≤ 16V — Demodulator Sensitivity V _{SENSE2} 6V ≤ V _{SUP} < 6.5V	Parameter Symbol Test Conditions and Comments Min Typ Input Voltage Range VINRD — 3 4 Input Modulation Frequency FMOD — 0.5 4 Demodulator Sensitivity VSENSE1 6.5V ≤ VSUP ≤ 16V Sensitivity is measured in the following application conditions: IANTENNA = 50mA peak, Vgp = 4V peak, CEXT = 10nF, and square wave modulator Sensitivity — 5 Demodulator Sensitivity VSENSE2 6V ≤ VSUP ≤ 6.5V The sensitivity is measured in the following application conditions: IANTENNA = 50mA peak, VRD = 4V peak, CEXT = 10nF, and square wave modulation FMOD = FTD1/32. See Figure 12 — 7 Demodulator Sensitivity VSENSE2 6V ≤ VSUP ≤ 6.5V The sensitivity is measured in the following application conditions: IANTENNA = 50mA peak, VRD = 4V peak, CEXT = 10nF, and square wave modulation FMOD = FTD1/32. See Figure 12 — 7.5 Demodulation Delay tDemod Configuration C Not including the delay due to the slew rate of the K output for configurations A and B See figure 12 — 394 After Write Pulse Settling Time tSettling1 — — 646 VartA11 meets the specification (see page 15). — 641 — 642 Dutput Carrier Frequency to Crysta	ParameterSymbolTest Conditions and CommentsMinTypMaxDemodulator (pin RD)Input Voltage RangeVINRD345Input Modulation FrequencyF _{MOD} 0.548Demodulator SensitivityVSENSE16.5V < VSUP ≤ 16V Sensitivity is measured in the following application conditions: IANTENNA = 50MA peak, VRD = 4V peak, CEXT = 10nF, and square wave medulator FMDD = FTD/32. See Figure 12515Demodulator SensitivityVSENSE26V ≤ VSUP < 6.5V The sensitivity is measured in the following application conditions: IANTENNA = 50mA peak, VFD = 4V peak, CEXT = 10nF, and square wave modulation FMOD = FTD/32. See Figure 12730Demodulator Delayt_DemodConfiguration C Not including the delay due to the sew rate of the K output for configuration S A and B See figure 127.510After Write Pulse Settling TimeIsetting2Clock stable condition implies VTAL1 meets the specification (see page 15)646700Output Carrier Frequency to Crystal Frequency RatioRFTD/FXT AL644Turn on/off Delayton/off250Driver1/2 Low Side Out. ResistanceRTDLIL_DAD = 150mA DC2.44	ParameterSymbolTest Conditions and CommentsMinTypMaxUnitDemodulator (pin RD)Input Voltage Range V_{INRD} 345VInput Modulation Frequency F_{MOD} 0.548kHzDemodulator SensitivityVSENSE1 $6.5V \le V_{SUP} \le 16V$ Sensitivity is measured in the following application conditions: $I_{ANTENNA} = 50mA$ peak, $V_{DD} = 4V$ peak, $C_{EXT} = 10nF,$ and square wave-515mVDemodulator Sensitivity V_{SENSE2} $6V \le V_{SUP} < 6.5V$ The tofolding application conditions: $I_{ANTENNA} = 50mA$ peak, $V_{DD} = 4V$ peak, $C_{EXT} = 10nF,$ and square wave-730mVDemodulator Sensitivity V_{SENSE2} $6V \le V_{SUP} < 6.5V$ The sensitivity is measured in the following application conditions: $I_{ANTENNA} = 50mA$ peak, $V_{RD} = 4V$ peak, $C_{EXT} = 10nF,$ and square wave modulation $F_{MOD} = F_{TD}/32$ See Figure 12-730mVDemodulation Delay t_{Demod} Configuration C Not including the delay due to the severate of the K output for configuration S (see page 15)646700 μ sRecovery Time after wake-up or reset from clock stable to demodulator valid outputIsetting2Clock stable condition implies V_{TAL1} meets the specification (see page 15)644Output Carrier Frequency to Crystal Frequency Ratio $R_{FTD/FXT}$ AL644Driver1/2 Low Side Out. Resistan

Table 9. Tag Reader Specifications

ISO 9141 Interface



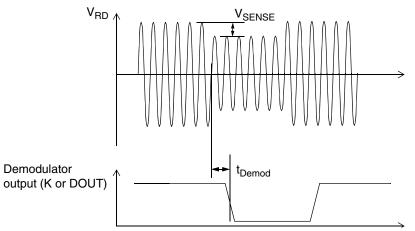


Figure 12. Demodulator Parameters Definition

16 ISO 9141 Interface

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted

	Parameter	Symbol	Test Conditions and Comments	Min	Тур	Max	Unit	Туре
		Rec	eiver (pins K and AM)					
4.0	Input Low Voltage	V _{IL}	_			0.3 x V _{SUP}	V	_
4.1	Input High Voltage	V _{IH}	_	0.65 x V _{SUP}		40	V	—
4.2	Input Hysteresis Voltage	V _{HY1}	_	0.4	0.65	1.3	V	—
4.3	Biasing Current	Ι _Β	$0V \le V_{IN} \le 16V$	1	3	5	μA	—
4.31	Input Current	I _{BM}	$-3 \le V_{IN} < 0$	-2	-1	—	mA	—
4.4	K to Rx delay	tdkrx	—		2	10	μS	—
		÷	Driver (pin K)					
5.0	Output Falling Edge Slew Rate	SR _F	$R_{Pull-up} = 510\Omega,$	3.5	5	6.5	V/µs	—
5.1	Output Rising Edge Slew Rate	SR _R	Calculated from 20% to 80% of the output swing.	3.5	5	6.5	V/µs	—
5.2	Rise Fall Slew Rates Symmetry	SR _{SYMET} RY		-1	0	1	V/µs	—
5.3	Output Low Voltage	V _{OLK}	$I_{LOAD} = 25 mA$	—	1.1	1.4	V	—
5.4	Input Current (driver switched on or off)	I _{IK}	$-3V \le V_{IN} \le 0V$	-2	_	0	mA	—
5.5	Current Limitation Threshold	١L	$0V \leq V_{IN} \leq 40V$	35	50	65	mA	—
5.6	Thermal Shutdown Threshold	TH _{SDWN}	—	130	150	170	°C	—

Table 10. ISO 914	1 Interface S	pecifications
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MC33690 Standalone Tag Reader Circuit, Rev. 5

Freescale Semiconductor



Digital I/O

17 Digital I/O

Typical values reflect average measurements at $6V \le V_{SUP} \le 16V$, $V_{SS} = 0V$, $T_J = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted

	Characteristic	Symbol	Test Condition and Comments	Min	Тур	Max	Unit	Туре
		Input (pin	s MODE1, MODE2, AM, TX)				•	•
6.0	Input Low Voltage	V _{ILD}	-	0		0.3 x V _{DD}	V	—
6.1	Input High Voltage	V _{IHD}	_	0.7 x V _{DD}	_	V _{DD}	V	—
6.2	Input Hysteresis Voltage	V _{HD}	_	.24	.7	1	V	—
	1	Ou	tput (pins DOUT,RX)	1		1		1
7.0	Output Low Voltage	V _{OL}	I _{LOAD} = 500uA	0	0.5	0.2 x V _{DD}	V	—
7.1	Output High Voltage	V _{OH}	I _{LOAD} = -500uA	0.8 x V _{DD}	4.6	V _{DD}	V	—
7.2	Fall/Rise Time	t _{F/R}	C _{LOAD} =10pF, Calculated from 10% to 90% of the output swing	_	—	150	ns	—

Table 11. Digital I/O Specifications



The internal circuits connected to the pins of the device are shown in Figures 13 - 23, including the diodes used for ESD protection.

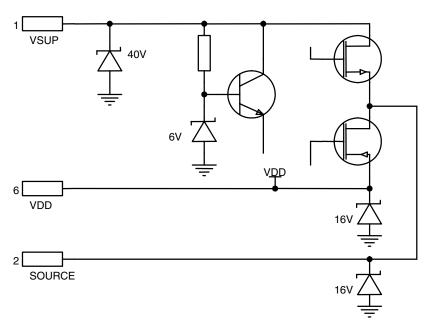


Figure 13. VSUP, VDD, and Source Internal Circuits

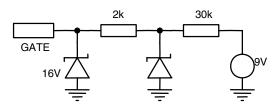
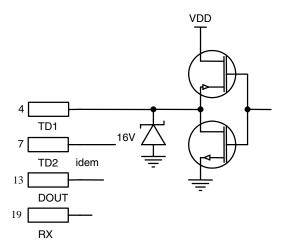
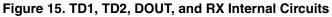


Figure 14. GATE Internal Circuits





MC33690 Standalone Tag Reader Circuit, Rev. 5

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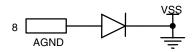


Figure 16. AGND Internal Circuits

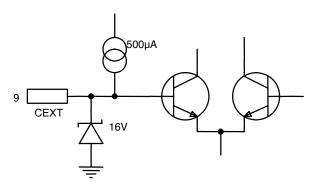


Figure 17. CEXT Internal Circuits

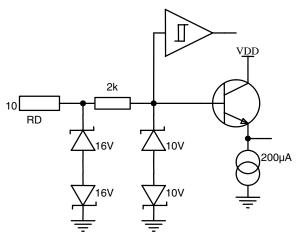
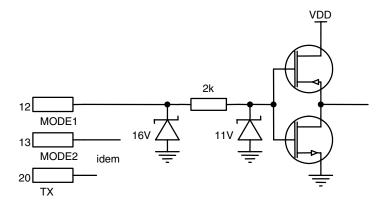
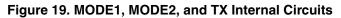


Figure 18. RD Internal Circuits







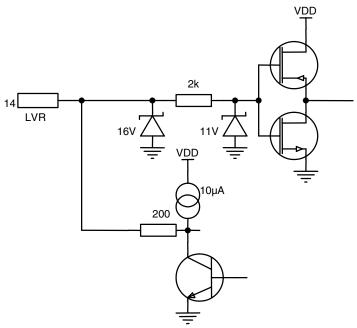


Figure 20. LVR Internal Circuits

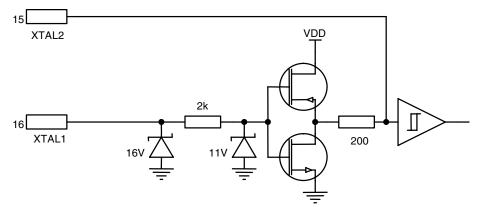


Figure 21. XTAL2 and XTAL1 Internal Circuits



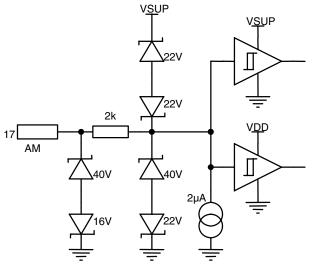


Figure 22. AM Internal Circuits

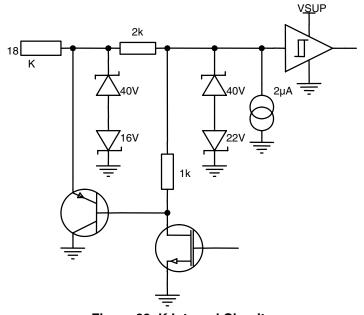
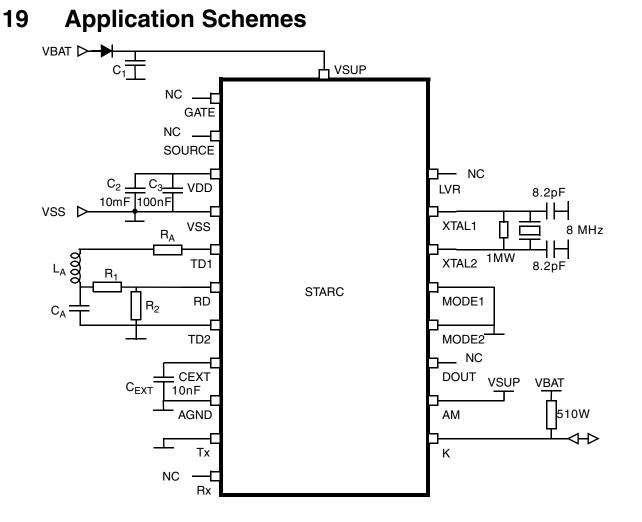


Figure 23. K Internal Circuits



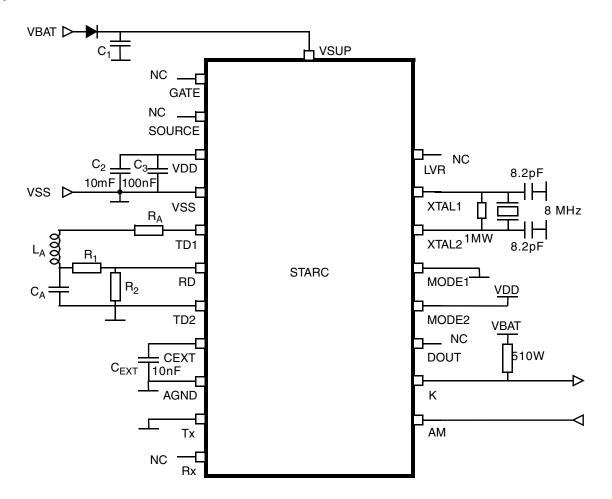


Note: If no external MOS transistor is necessary to increase the voltage regulator current capability, the pins GATE and SOURCE must be left unconnected. In this configuration, the outputs Rx and DOUT force a low level. C1 is not required for the STARC functionality and only acts as a reservoir of energy. To preserve the demodulator sensitivity, CEXT and R2 should be connected to AGND and VSS connected to AGND using a low resistance path.

Figure 24. Standalone Configuration with One-Wire Bus



Application Schemes

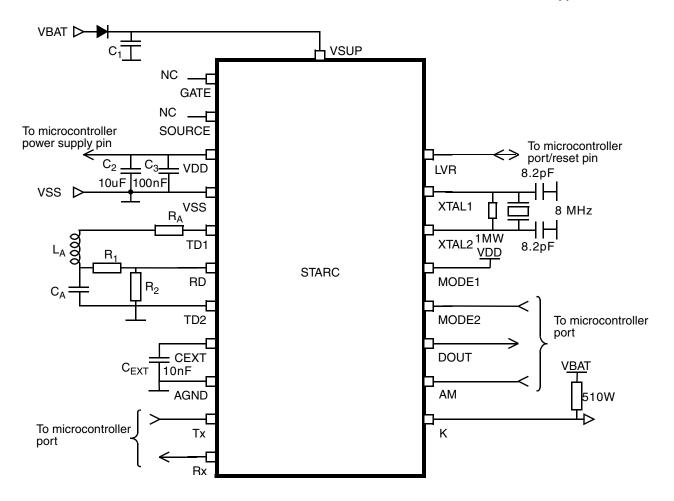


Note: If no external MOS transistor is necessary to increase the voltage regulator current capability, the pins GATE and SOURCE must be left unconnected. C₁ is not required for the STARC functionality and only acts as a reservoir of energy. To preserve the demodulator sensitivity, C_{EXT} and R₂ should be connected to AGND and VSS connected to AGND using a low resistance path.

Figure 25. Standalone Configuration with Two-Wires Bus



Application Schemes



Note: If no external MOS transistor is necessary to increase the voltage regulator current capability, the pins GATE and SOURCE must be left unconnected. C₁ is not required for the STARC functionality and only acts as a reservoir of energy. To preserve the demodulator sensitivity, C_{EXT} and R₂ should be connected to AGND and VSS connected to AGND using a low resistance path.

Figure 26. Direct Connection to a Microcontroller

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